



500.37328CX1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): YOKOGAWA, et al  
Serial No.: 09/336,687  
Filed: June 21, 1999  
For: PLASMA PROCESSING SYSTEM AND METHOD  
Group: 1763  
Examiner: L. Alejandro

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AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

January 13, 2003

Sir:

The following amendments and remarks are respectfully submitted in connection with the above-identified application in response to the Office Action dated September 11, 2002.

IN THE SPECIFICATION:

Page 13, please amend the paragraph beginning at line 13 as follows:

DI In this embodiment of the present invention, a ring-shaped member 12 shown in Fig. 1 is arranged in the periphery of sample 6. Member 12 has a surface made of silicon 13 which is brought into contact with the plasma. The configuration further includes a capacitor 14 to divide the bias applied to sample 6 to apply resultant bias to silicon film 13. Disposed just below member 12 is a temperature controller 15 to keep temperature of member 12 at a fixed value. A silicon wafer as sample 6 is ordinarily covered with a resist mask. The amount of radicals of the plasma incident to the surface of sample 6 is influenced by reaction with the resist mask. Fluorine radicals derived from the plasma of fluorocarbon gas such as C<sub>4</sub>F<sub>8</sub> are consumed through reaction with the resist. The amount of fluorine radicals effectively incident to